

Description

The DMP22D6UT uses advanced trench technology to provide excellent $R_{\text{DS}(\text{ON})}\text{, low gate charge and}$

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



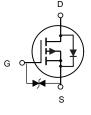
SOT-523

General Features

 $V_{DS} = -20V I_{D} = -0.66A$

 $R_{DS(ON)}$ < 560 mQ@ V_{GS} =-4.5V $R_{DS(ON)}$ < 780 mQ@ V_{GS} =-2.5V

ESD Rating: 1500V HBM



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP22D6UT	SOT-523	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _D s	Drain-Source Voltage	-20	V	
V _G s	Gate-Source Voltage	±12	V	
l _D	Drain Current-Continuous	-0.66	А	
P _D	Maximum Power Dissipation	150	mW	
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	833	°C/W	



Electrical Characteristics (T_J=25°C, unless otherwise noted)

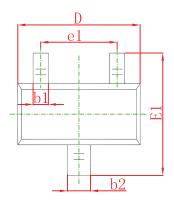
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
Gate-body leakage current	Igss	V _{GS} =±10V, V _{DS} = 0V			±10	μA
Gate threshold voltage (note2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1.0	V
Drain-source on-resistance (note2)	R _{DS(on)}	V _{GS} =-4.5V, I _D =-0.5A			0.56	Ω
		V _{GS} =-2.5V, I _D =-0.2A			0.78	Ω
Maximum Continuous Drain to Source Diode Forward Current	Is				-0.6	Α
Maximum Pulsed Drain to Source Diode Forward Current	Ism				-1.2	Α
Diode forward voltage	V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V
DYNAMIC CHARACTERISTICS (note4)						
Input capacitance	C _{iss}			115		pF
Output capacitance	Coss	V _{DS} =-16V,V _{GS} =0V, f =1MHz		15		pF
Reverse transfer capacitance	C _{rss}	1 - 11/11/12		9		pF
SWITCHING CHARACTERISTICS (no	te4)		1		1	
Turn-on delay time (note3)	t _{d(on)}			9		nS
Turn-on rise time (note3)	t _r	V _{GS} =-4.5V,V _{DS} =-10V,		6		nS
Turn-off delay time (note3)	t _{d(off)}	I_D =-200mA, R_{GEN} =10 Ω		33		nS
Turn-off fall time (note3)	t _f			22		nS

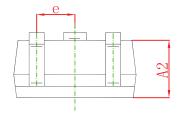
Notes:

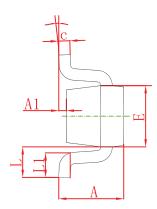
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300 μ s, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.



SOT-523 Package Information

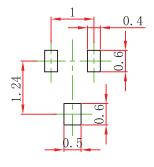






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.700	0.900	0.028	0.035	
A1	0.000	0.100	0.000	0.004	
A2	0.700	0.800	0.028	0.031	
b1	0.150	0.250	0.006	0.010	
b2	0.250	0.350	0.010	0.014	
С	0.100	0.200	0.004	0.008	
D	1.500	1.700	0.059	0.067	
E	0.700	0.900	0.028	0.035	
E1	1.450	1.750	0.057	0.069	
е	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043	
L	0.400 REF.		0.016 REF.		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

SOT-523 Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

P-Channel Enhancement Mode MOSFET

Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by HXY MOS manufacturer:

Other Similar products are found below:

IRFD120 JANTX2N5237 BUK455-60A/B MIC4420CM-TR VN1206L NDP4060 SI4482DY IPS70R2K0CEAKMA1 SQD23N06-31L-GE3
TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 DMN1053UCP4-7 SQJ469EP-T1-GE3 NTE2384 DMC2700UDMQ-7
DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-TP MCQ7328-TP BXP7N65D BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L
BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13 SLF10N65ABV2
BSO203SP BSO211P IPA60R230P6 IPA60R460CE